

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-8 (Canceled).

Claim 9 (Currently Amended): A method according to claim [[16]] 17, wherein the ion implantation includes implanting ions chosen from among the following species: hydrogen and rare gases.

Claim 10 (Currently Amended): A method according to claim [[16]] 17, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (Currently Amended): A method according to claim [[16]] 17, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out before the thinning down the thin film.

Claim 13 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out after the thinning down the thin film.

Claims 14-16 (Canceled).

Claim 17 (New): A method for transferring an electrically active thin film from an initial substrate of SiC to a target substrate, including the steps of:

Ion implantation through a face of the initial substrate to create a buried, embrittled film at a determined depth in relation to the implanted face of the initial substrate, said thin film being delimited between the implanted face and the buried film;

fastening the implanted face of the initial substrate to a face of the target substrate;

separating the thin film from a remainder of the initial substrate at a level of the buried film; and

thinning down the thin film transferred on the target substrate,

wherein the ion implantation step is performed with selected dose, energy and implantation current such that the implantation defect concentration in the first 500 nm of implanted SiC is lower than $9 \cdot 10^{20}$ atoms/cm³, whereby a number of acceptor defects compatible with the desired electrical properties of the thin layer is obtained in the thin layer of SiC thinned to a thickness lower than 500 nm.